EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	9	MEMS and getter and cavity and cover and (substrate or wafer or semiconductor) and chamber and vacuum and "inert gas" and (temperature or heat or degree) and bond$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/29 12:28
S2	109	getter and cavity and cover and (substrate or wafer or semiconductor) and chamber and vacuum and "inert gas" and (temperature or heat or degree) and bond$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 14:47
S3	1	getter and cavity and cover and (substrate or wafer or semiconductor) and chamber and vacuum and "inert gas" and (temperature or heat or degree) and bond$4 and titanium and time and argon and discharg$4 and anodic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 14:48
S4	25	getter and cavity and cover and (substrate or wafer or semiconductor) and chamber and vacuum and "inert gas" and (temperature or heat or degree) and bond$4 and titanium and time and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/23 14:48
S5	144	adhes$4 and conduct$4 and binder and filler and (heat$4 or thermal or temperature) and pressuriz$4 and viscosity and connect and (hard$4 or solid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:08
S6	16	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject$4 and "inert gas" and bond	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:10
S7	10	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject$4 and "inert gas" and bond and argon and time and degree	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:10

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S8	3	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject$4 and "inert gas" and bond and argon and time and degree and anodic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:11
S9	7	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject$4 and argon and time and degree and anodic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:12
S10	7	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject$4 and argon and degree and anodic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:12
S11	14	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject$4 and argon and degree	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:13
S12	14	MEMS and (getter or titanium) and cavity and cover and substrate and (vacuum near chamber) and inject$4 and argon and degree and bond	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:17
S13	7	MEMS and titanium and cavity and cover and (substrate or semiconductor or wafer) and "vacuum chamber" and argon and degree and anodic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:24
S14	16970	getter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:25
S15	216	(getter near titanium)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:26

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S16	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and "vacuum chamber" and degree and bond	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:29
S17	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and (vacuum near chamber) and degree and bond	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:29
S18	3	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:31
S19	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and "vacuum chamber"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:31
S20	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and (vacuum near chamber)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:32
S21	2	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:32
S22	2	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum and chamber	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:32
S23	1	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum and chamber and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:32

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S24	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum and chamber and argon and degree	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:32
S25	0	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum and chamber and argon and (bond or attach)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 09:33
S26	1	(getter near titanium) and cavity and cover and (substrate or semiconductor or wafer) and vacuum and chamber and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:12
S27	0	(getter near titanium) and (cover near glass) and "anodic bond"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:13
S28	0	getter near glass and "anodic bond"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:13
S29	220	"anodic bond"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:13
S30	9	"anodic bond" and getter	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:14
S31	6	"anodic bond" and getter and glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:14

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S32	6	"anodic bond" and getter and glass and cover	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:14
S33	6	"anodic bond" and getter and glass and cover and substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/06/13 10:15
S34	2	(("5701008") or ("6499354B1")).PN. or ((2002/0089835A1) or (2003/0085438A1)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/02/16 10:51
S35	0	S34 and getter and cavity and cover and (substrate or semiconductor or wafer) and degree and titanium and argon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2006/02/16 10:59
S36	90	getter and cavity and cover and (substrate or semiconductor or wafer) and degree and titanium and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 11:00
S37	17	getter and cavity and cover and (substrate or semiconductor or wafer) and degree and titanium and argon and (vacuum near chamber) and glass and (heat or thermal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 11:11
S38	1	getter and cavity and cover and (substrate or semiconductor or wafer) and degree and titanium and argon and (vacuum near chamber) and bond and align	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 11:12
S39	44	getter and cavity and cover and (substrate or semiconductor or wafer) and degree and (argon or gas or inert) and (vacuum near chamber) and bond and align	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 11:29
S40	14	(getter near4 cavity) and (vacuum near chamber) and cover and degree	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 11:33

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S41	9	(getter near4 cavity) and (vacuum near chamber) and cover and degree and titanium	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 11:33
S42	3	(getter near4 cavity) and (vacuum near chamber) and cover and degree and titanium and argon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/02/16 11:33